

High-Efficiency Inverter Controller

FEATURES

- Single-stage power conversion, input voltage range of 5V to 18V
- Reduces the number of components and board size by 30% compared with conventional design
- Supports both floating and grounded secondary designs
- 90% efficiency vs. typical 75% efficiency of conventional designs
- Internal open-lamp and short-circuit protections
- Wide dimming range
- Supports synchronization among multiple inverter modules
- Reliable 2-winding transformer design, eliminates arcing problems
- Constant frequency, symmetrical, sinusoidal drive

GENERAL DESCRIPTION

The OZ962 is a unique high-efficiency, CCFL backlight controller. It generates symmetrical, near sinusoidal output voltage and current waveforms for driving a CCFL backlight. The OZ962 operates in a single, constant frequency, pulse-width-modulation (PWM) mode. Typical operating frequency ranges between 30 KHz to 100 KHz, depending on the CCFL and the transformer's characteristics.

Operating in a PWM push-pull manner, the transformer in the OZ962 backlight inverter requires only one primary winding and one secondary winding, with the secondary winding requiring no fold-back treatment.

The OZ962 is available in both 16-pin SOIC and TSSOP packages. It is specified over the commercial temperature range: 0 °C to +70 °C.

ORDERING INFORMATION

- OZ962R** - 16 lead TSSOP
- OZ962G** - 16-pin plastic SOP

TYPICAL APPLICATION CIRCUIT

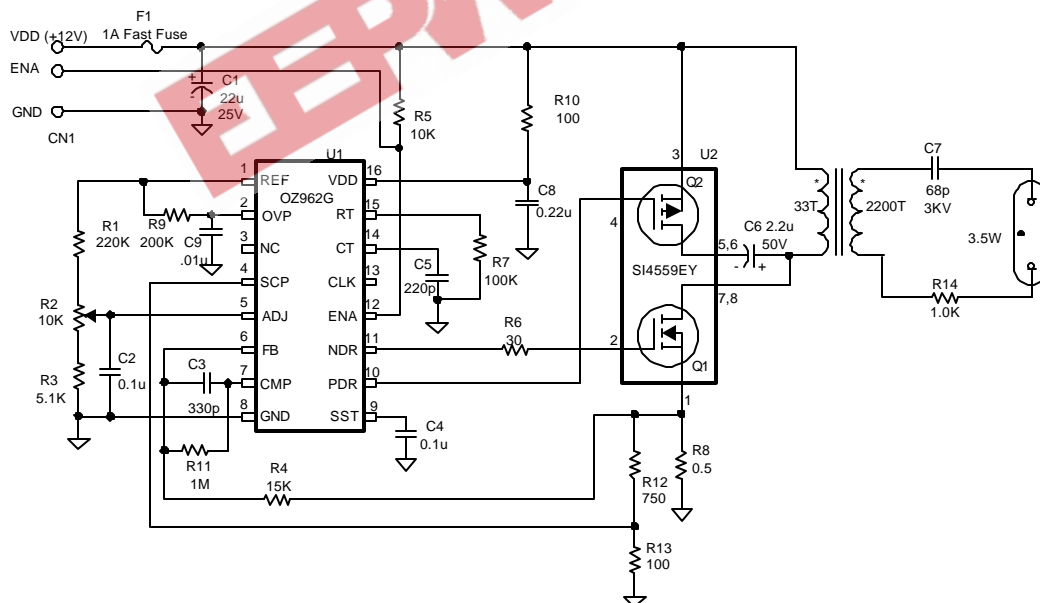
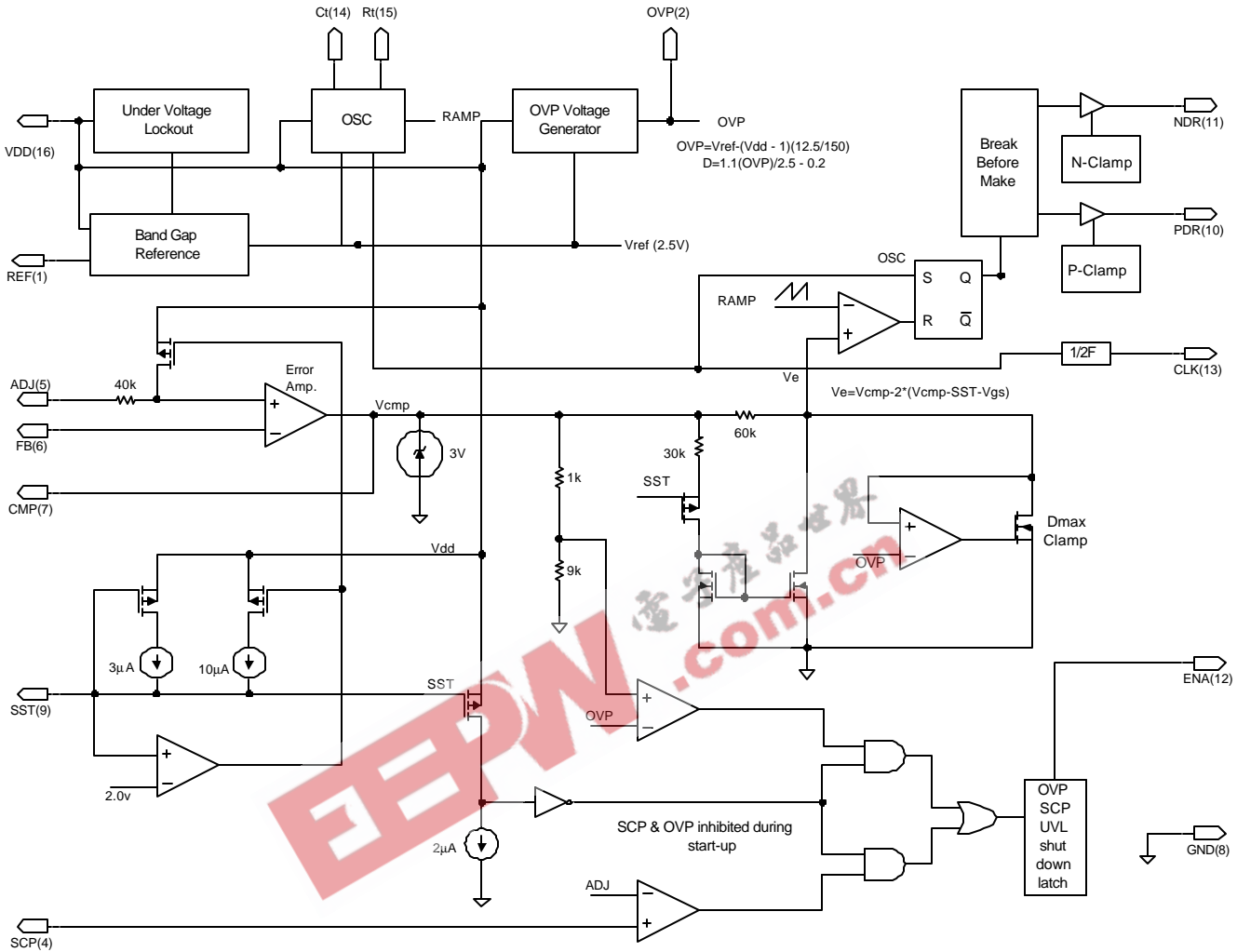


Figure 1. Typical Floating Secondary Application

FUNCTIONAL BLOCK DIAGRAM



Note:
OVP – Over Voltage Protection
SCP – Short-Circuit Protection
UVL – Under Voltage Lockout

Figure 2. Functional Block Diagram

PIN DESCRIPTION

Names	Pin No.	I/O	Description
REF	1	O	Reference voltage output. Nominal voltage is 2.5 V.
OVP	2	I	Over-voltage protection setting. Refer to formula for OVP in block diagram on page 2 of this document.
NC	3	-	No connection.
SCP	4	I	Short-circuit protection input.
ADJ	5	I	Reference voltage input for dimming control.
FB	6	I	Current sense feedback.
CMP	7	O	Compensation for the current sense feedback.
GND	8	GND	Ground.
SST	9	I	$T_{sst} \approx 0.2 C_{sst} (V_{dd} - 5)$, where C_{sst} is the soft start capacitor value in μF and T_{sst} value is in μs .
PDR	10	O	Gate drive output for the P-MOSFET.
NDR	11	O	Gate drive output for the N-MOSFET.
ENA	12	I	Enable input, active high (V_{th} is about 1.7 V).
CLK	13	O	Open-drain clock output.
CT	14	I/O	Timing capacitor. CT and RT set the clock frequency.
RT	15	I/O	Timing resistor.
VDD	16	PWR	Supply voltage input.

ABSOLUTE MAXIMUM RATINGS

VDD	18 V	Operating temp.	0 °C to 70 °C
GND	+/- 0.3 V	Operating junction temp.	150 °C
Logic inputs	-0.3 V to VDD+0.3 V	Storage temp.	-55 to 150 °C
Power dissipation	800 mW at 25 °C		

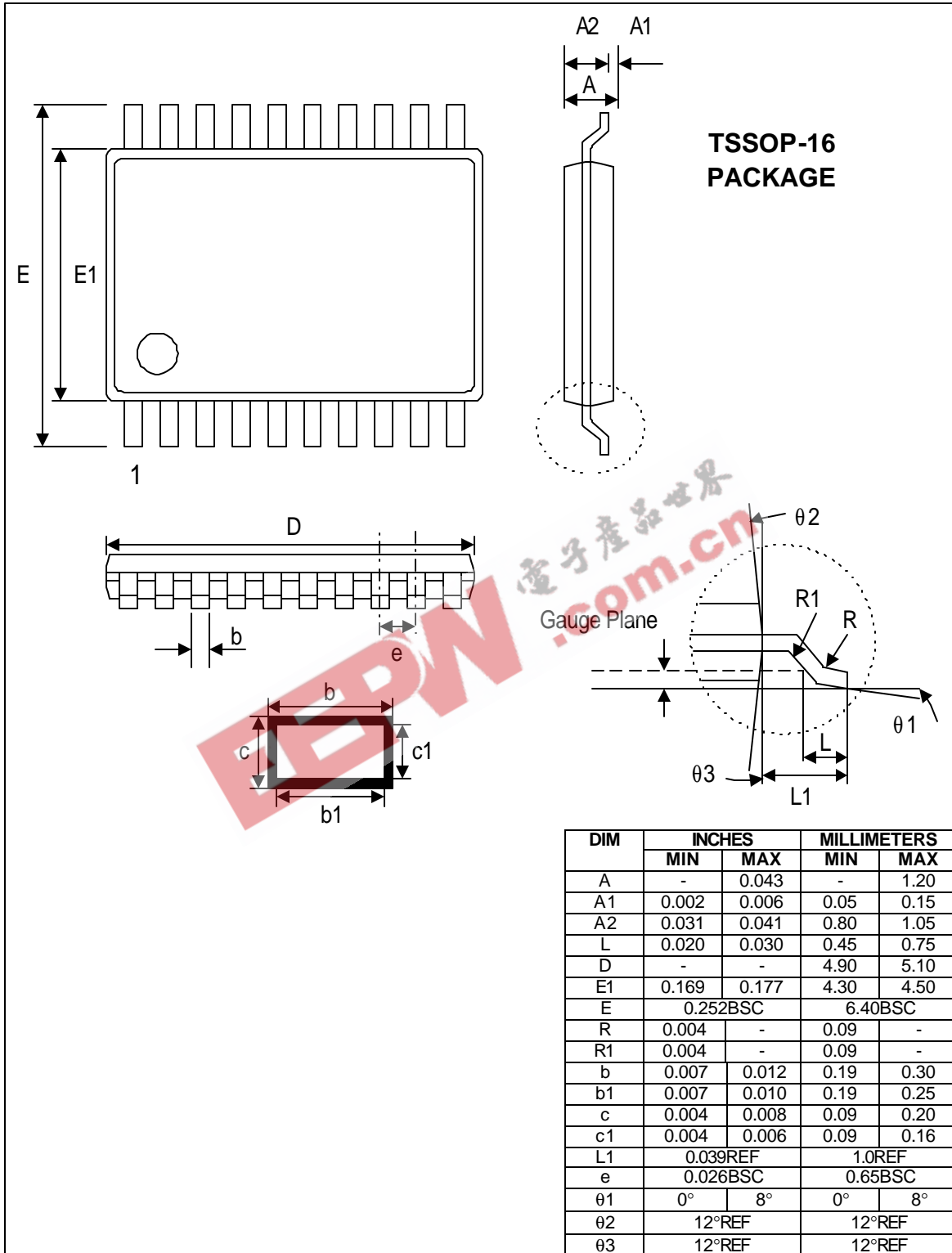
RECOMMENDED OPERATING RANGE

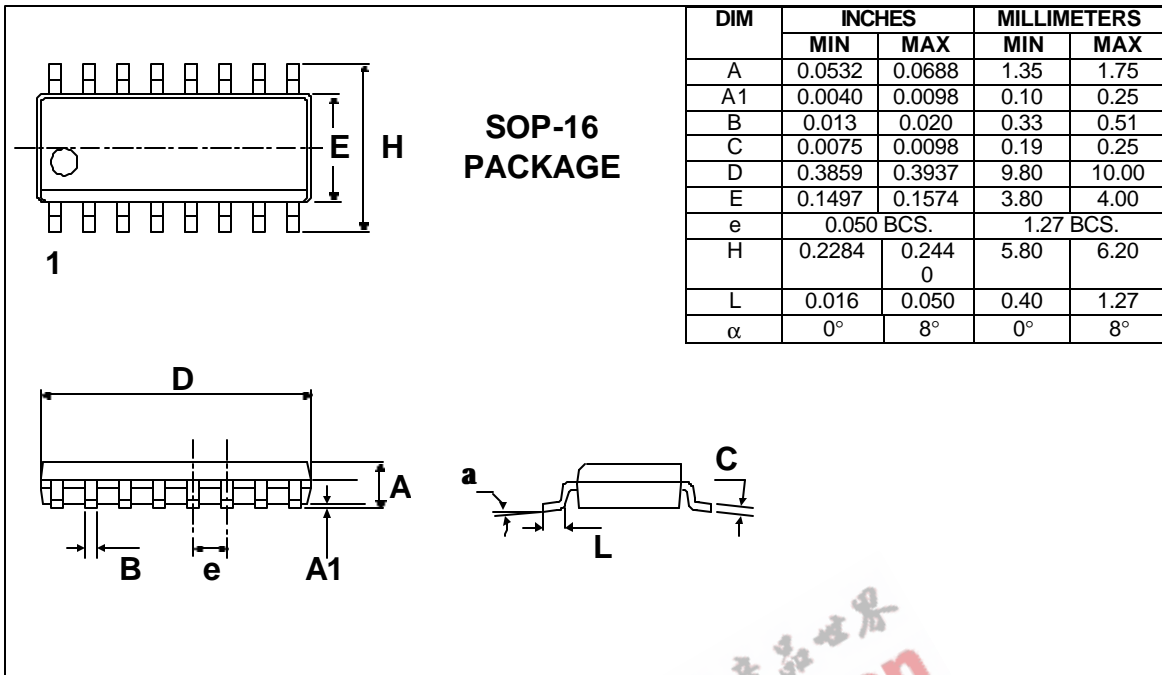
VDD	5V to 18V
Fosc	30 KHz to 100 KHz
Rosc	50 k to 150 k

FUNCTIONAL SPECIFICATIONS

Parameter	Symbol	Test Conditions 5 V < VDD < 15 V	Limits			Unit
			Min	Typ	Max	
Reference Voltage						
Nominal voltage	Vref	I _{load} = 0.25 mA, VDD = 5 V	2.37	2.50	2.63	V
Line regulation			-	8	-	mV/V
Load regulation		I _{load} = 0.2 mA to 1.0 mA	-	1	-	mV/mA
Oscillator						
Initial accuracy	fosc	Ct = 220 pF, Rt = 120 k	48	53	58	KHz
Ramp peak			2.45	2.55	2.65	V
Ramp valley			0.40	0.45	0.50	V
Temp. stability		TA = 0 °C to 70 °C	-	-	200	ppm/°C
Error Amplifier						
Input bias current		V _{ADJ} =V _{FB} =2.0 V	-	25	500	nA
Input offset voltage		V _{FB} = 4.0 V	-	5	10	mV
Input voltage range			0	-	VDD-1.5	V
Open loop voltage gain			50	60	-	dB
Unity gain bandwidth			1	1.5	-	MHz
Power supply rejection			50	60	-	dB
Under-Voltage Lockout						
Positive-going threshold voltage			-	3.8	4	V
Negative-going threshold voltage			3.4	3.6	-	V
Supply						
Supply current - Enable Low Adj, CT = Open	I _{OFF}	VDD = 5.0 V	-	25	120	μA
Supply current - Enable Low Adj, CT = Open	I _{OFF}	VDD = 15 V	-	25	120	μA
Supply current - Enable High	I _{ON}	VDD = 5.0 V	-	0.6	1.5	mA
Supply current - Enable High	I _{ON}	VDD = 15 V	-	0.6	1.5	mA
NDR output						
Output high voltage	V _{OH}	Isink = 10 mA, VDD < 7.8 V	VDD-0.3	VDD-0.5	-	V
		VDD > 7.8 V	7.0	8.0	9.0	V
Output low voltage	V _{OL}	I _{source} = 10 mA	-	0.3	0.8	V
Output resistance	R _{OUT}	VDD = 5.0 V	-	50	80	Ω
PDR output						
Output high voltage	V _{OH}	I _{sink} = 10 mA	VDD-0.6	VDD-0.3	-	V
Output low voltage	V _{OL}	I _{source} = 10 mA, VDD < 7.8 V	0.4	0.5	0.8	V
		VDD > 7.8 V	-	VDD-6.0	VDD-4.0	
Output resistance	R _{OUT}	VDD = 5.0 V	-	50	80	Ω
Break-Before-Make						
Qn off to Qp on delay	T _{HL}		200	240	280	ns
Qp off to Qn on delay	T _{LH}		220	260	300	ns

PACKAGE INFORMATION





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